



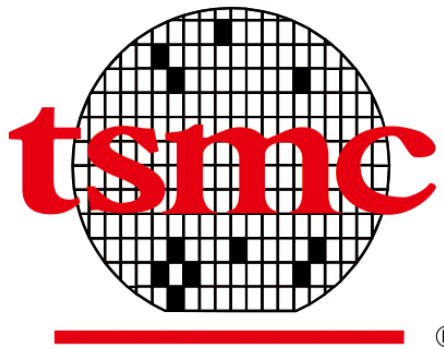
APEC 2026



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Implementing Vertical Power Delivery for AI Processors

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Unleash Innovation

Presentation Number (ex. IS01.1) from APEC Program

1: TSMC Incorporated
2: Princeton University

Outline of this Talk

- Need for Vertical Power Delivery
- Benefits of Integrated Voltage Regulators
- Ingredients for successful Implementation
- Wrap-Up with Q&A

Why: Projected Current Density



Losses based on extrapolated data from various sources and is not based on any system

Benefits of Vertically In-Package Regulators

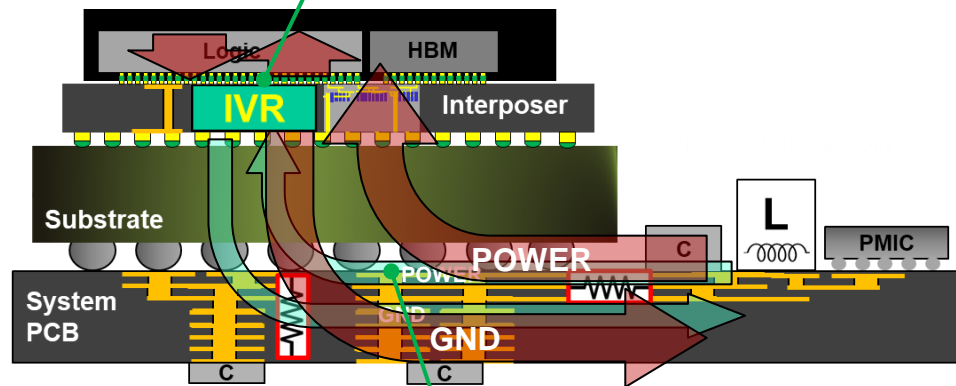
$$P_{loss} = I^2 R$$

$$P_{SoC} = \frac{1}{2} C V^2 F$$

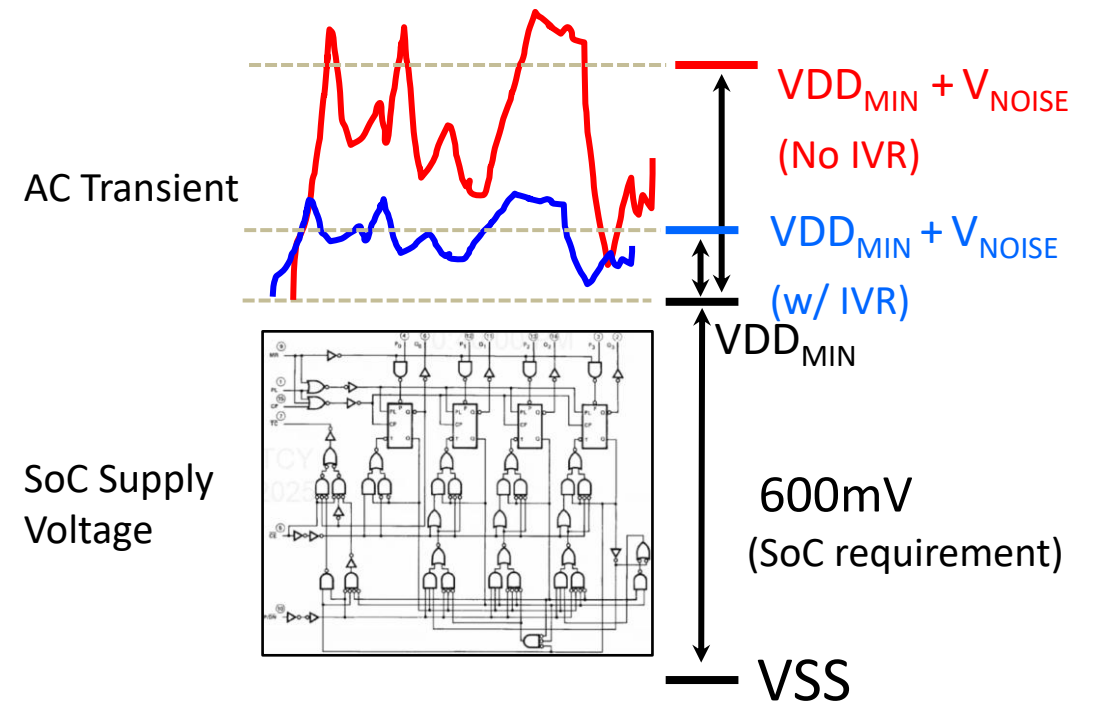
- Lowers I^2R loss
- Reduce EM constrain in power path

- Reduces Inductance Loop
- Lower transient noise → Lower VDD_{MIN}

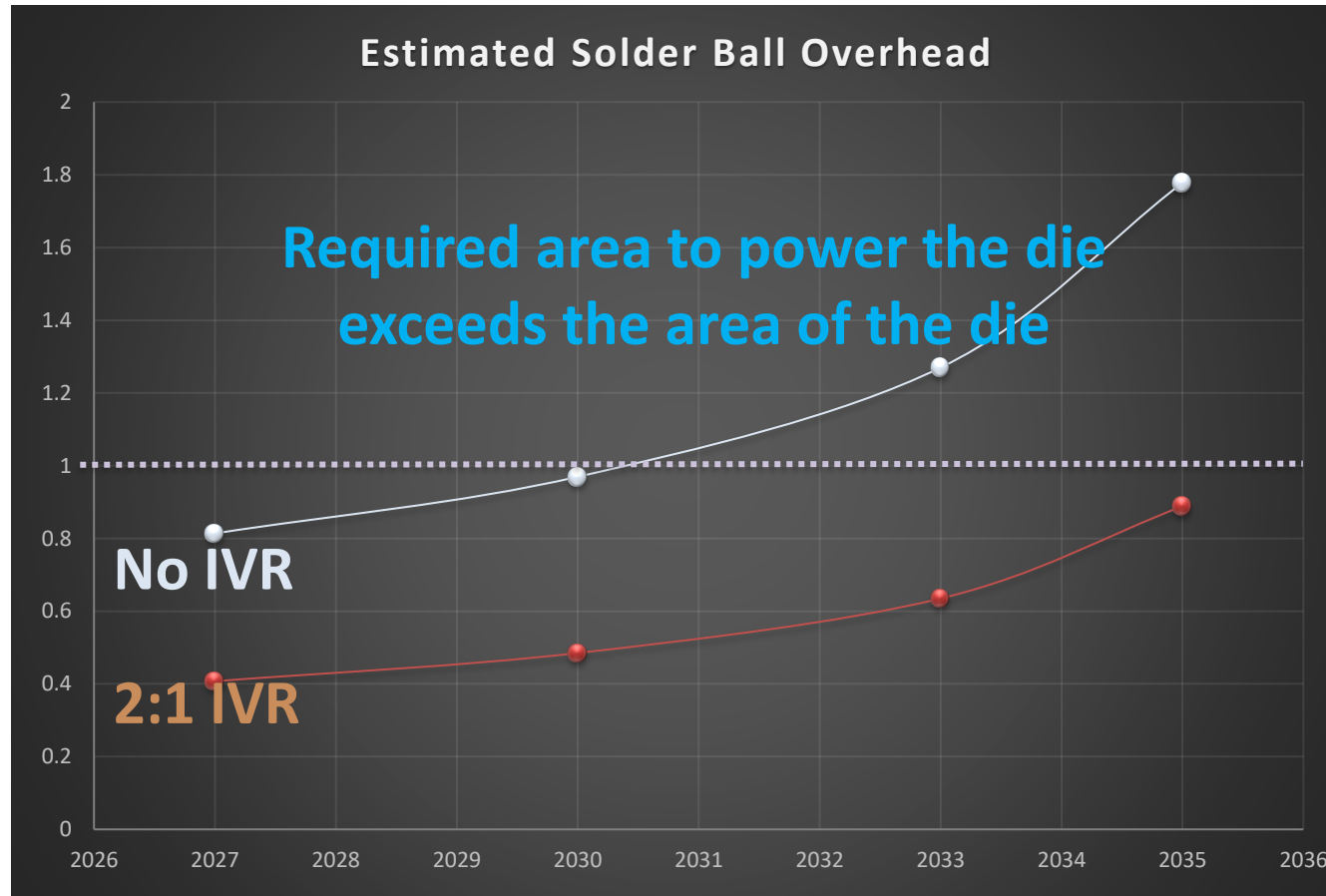
Reduce resistance of high current path



1.8V to 0.7V, 2.2x lower input current



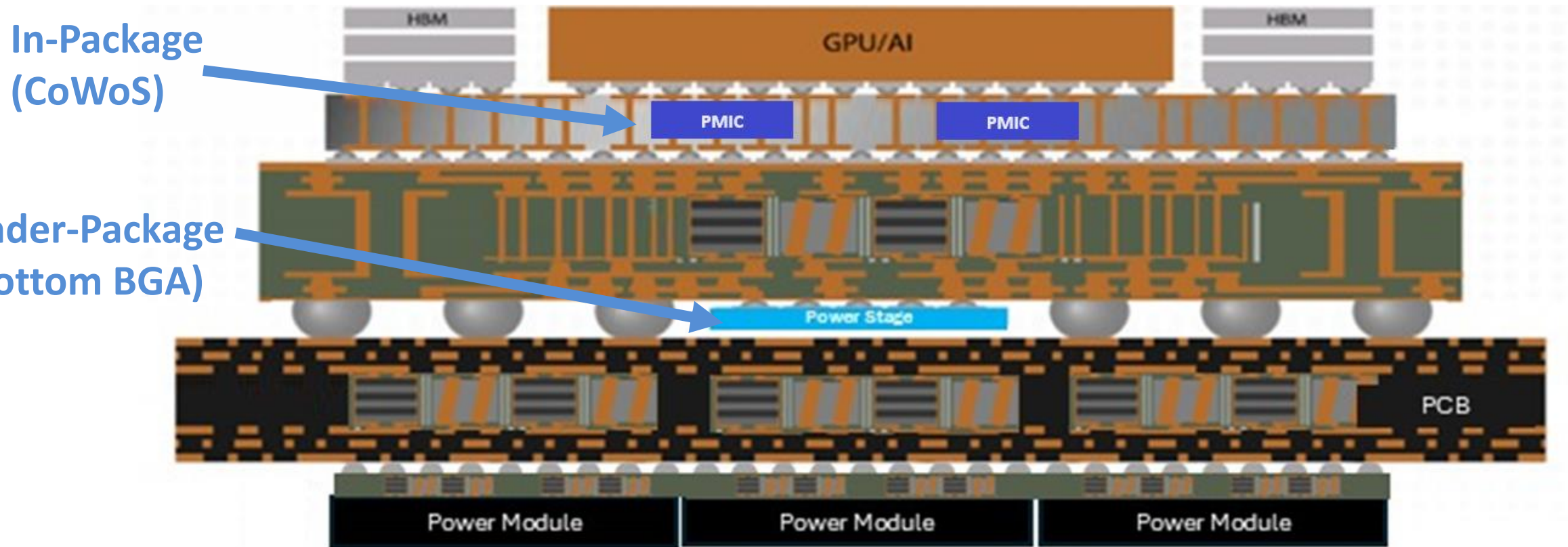
IVR Technology is a Must Have for Future AI Processors



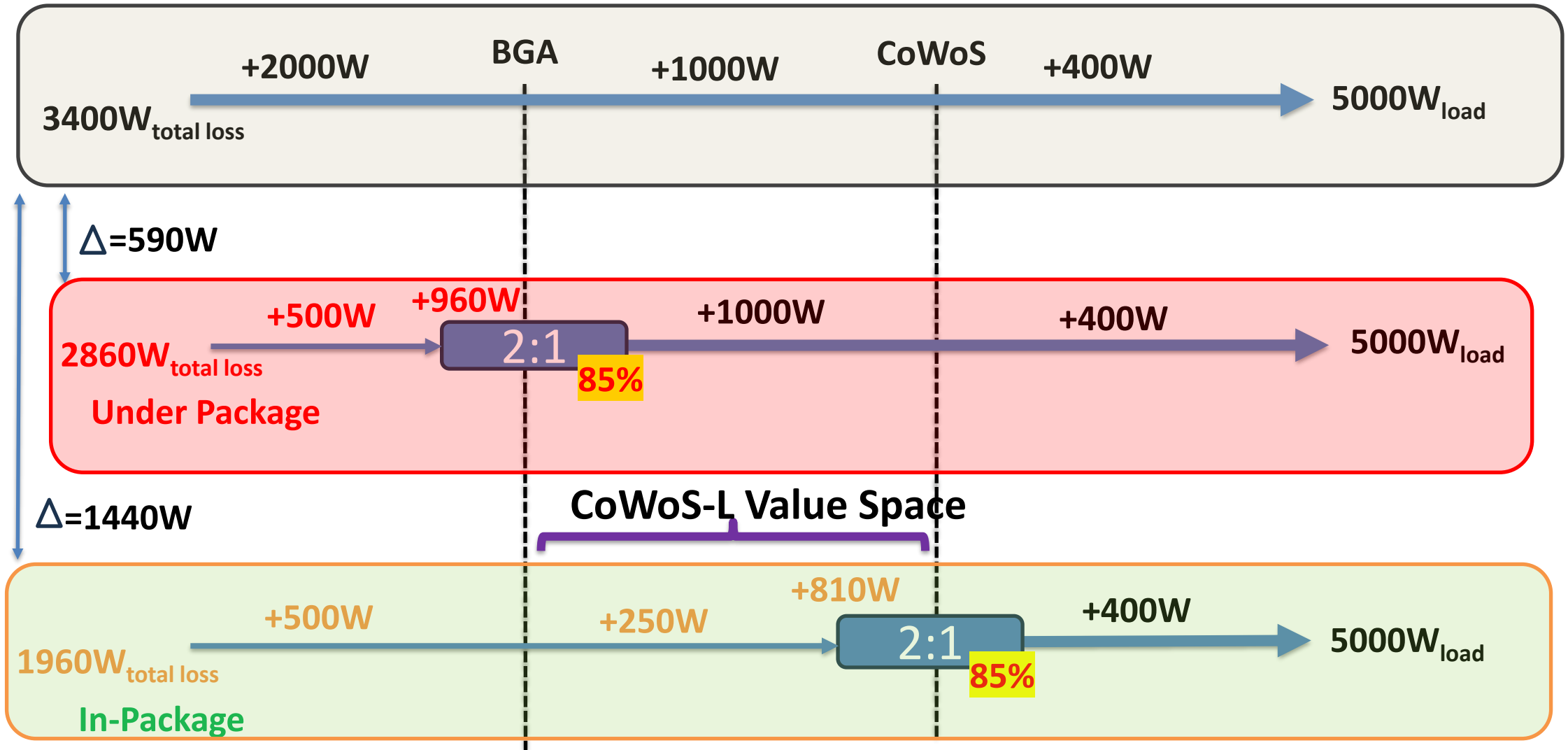
Maximum Solder Ball Current is limited by Thermal Mechanical Stress

More Balls → Larger Footprint → Larger PDN Resistance

Vertical Stack-Up

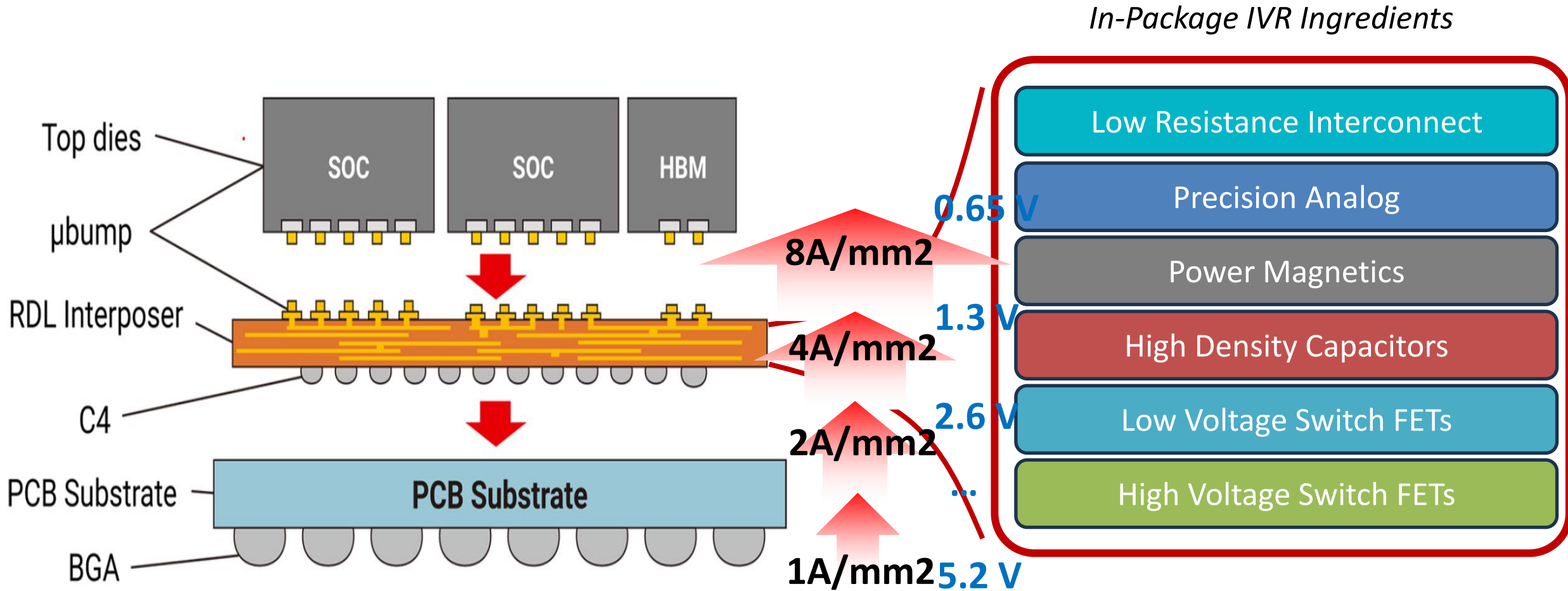


Why, now where

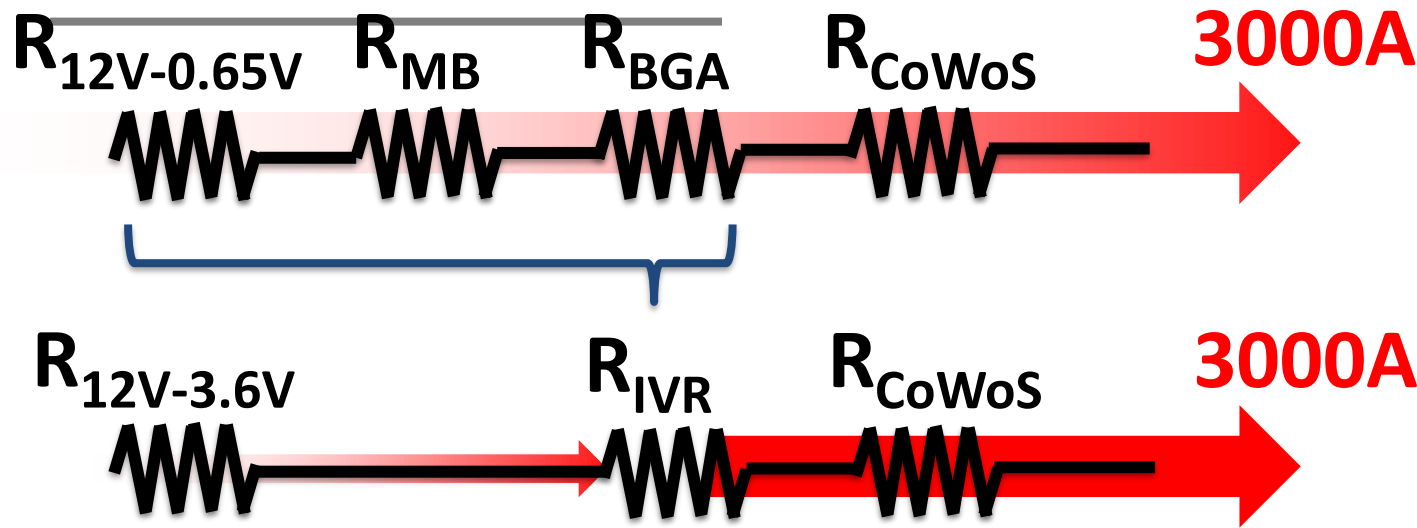


*Calculations are based on hypothetical 2:1 Regulator with 85% Efficiency system using estimated parasitics and losses from multiple sources

What Ingredients should be on the RoadMap

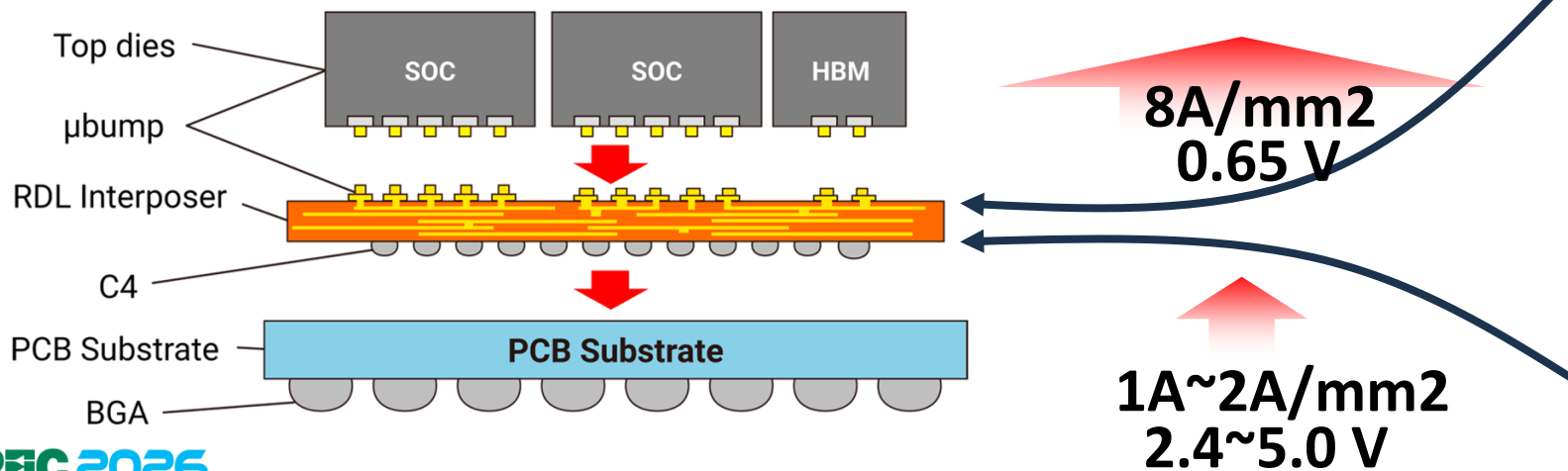


Full Load – Resistance Dominates Efficiency



- R_{IVR}**
- Magnetics**
Low DCR and ACR
- Interconnect**
Resistance & EM Rules
- Semiconductors**
Low R_{dson} and C_{oss}

$$R_{12V-3.6V} + R_{IVR} < R_{12V-3.6V} + R_{MB} + R_{BGA}$$

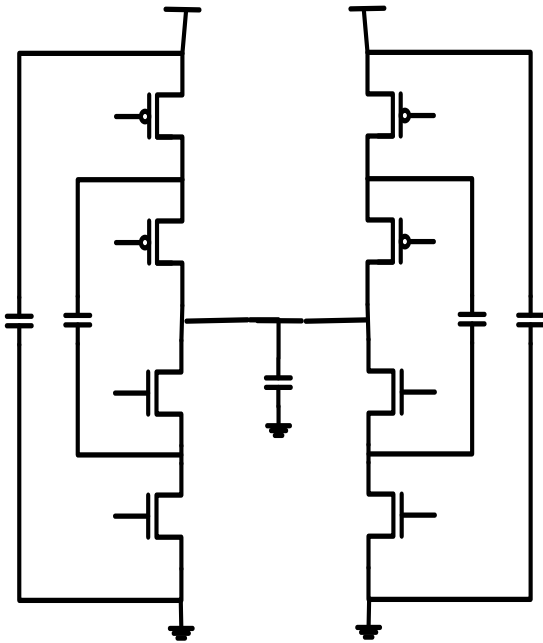


- Low Resistance Interconnect
- Precision Analog
- Power Magnetics
- High Density Capacitors
- Low Voltage Switch FETs
- High Voltage Switch FETs

Which Topology for 2:1

2:1 SwCap

2:1 Buck



Efficiency

SwCap

Buck



No magnetics
Discrete Regulation
Low Bandwidth
Requires >20x Capacitance

Lower ripple
Continuous Regulation
High Bandwidth
Current output

Low Resistance Interconnect

Precision Analog

Power Magnetics

High Density Capacitors ++

Low Voltage Switch FETs

High Voltage Switch FETs

Low Resistance Interconnect

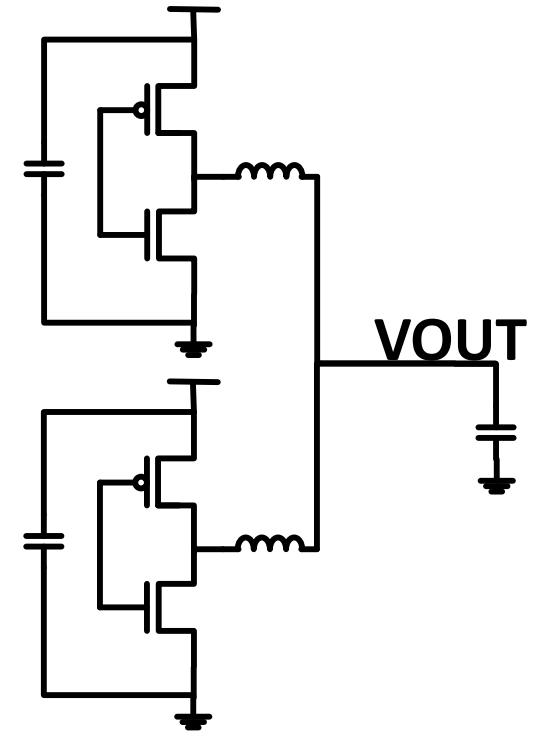
Precision Analog

Power Magnetics

High Density Capacitors

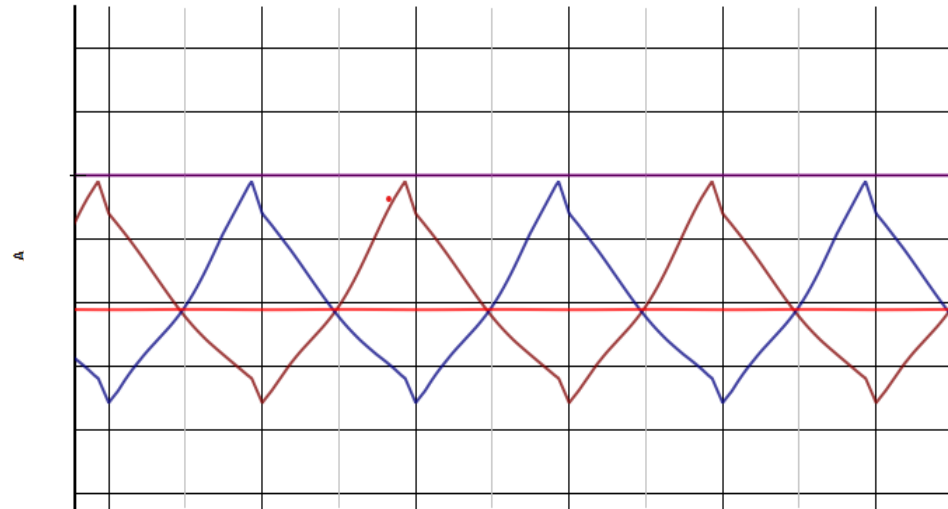
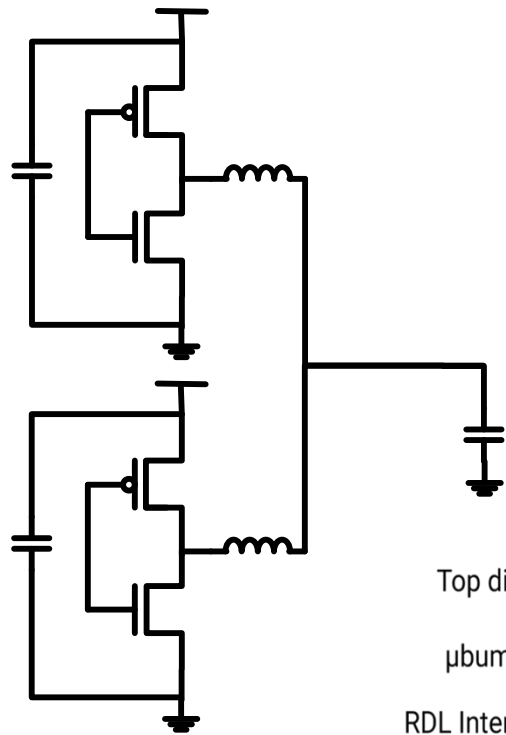
Low Voltage Switch FETs

High Voltage Switch FETs

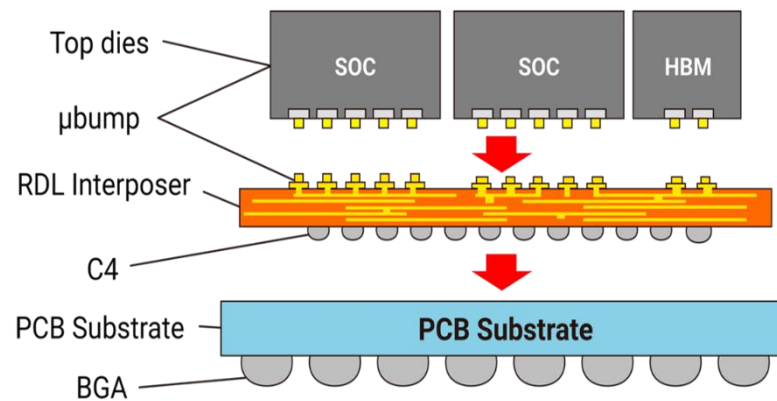


2:1 Switched Inductor

1.4V -> 0.7V



- Efficiency: Good
- Regulator Losses < I^2R Losses



2A~4A/mm²
0.65V

1A~2A/mm²
1.2V~1.8V

In-Package IVR Ingredients

Low Resistance Interconnect

Precision Analog

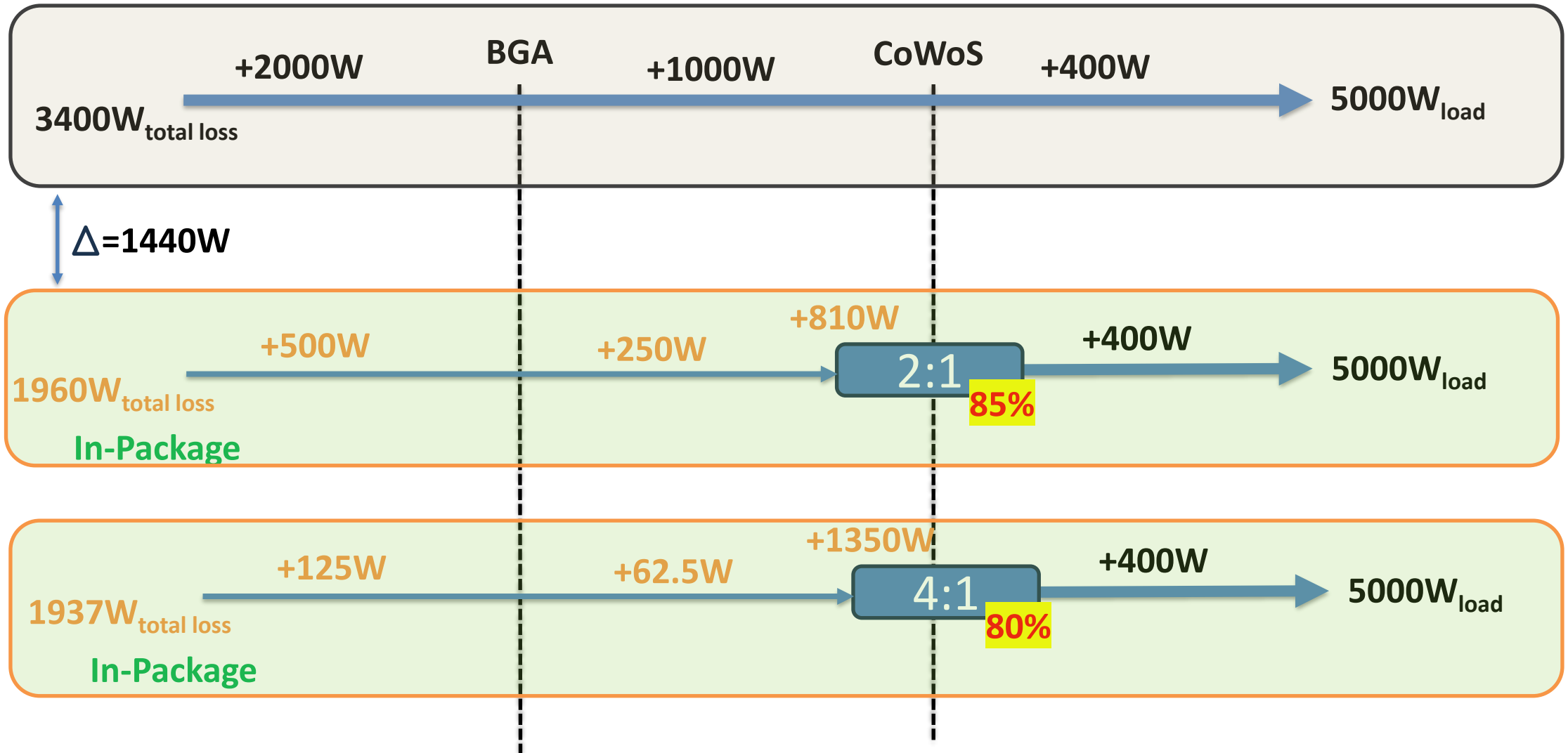
Power Magnetics

High Density Capacitors

Low Voltage Switch FETs

High Voltage Switch FETs

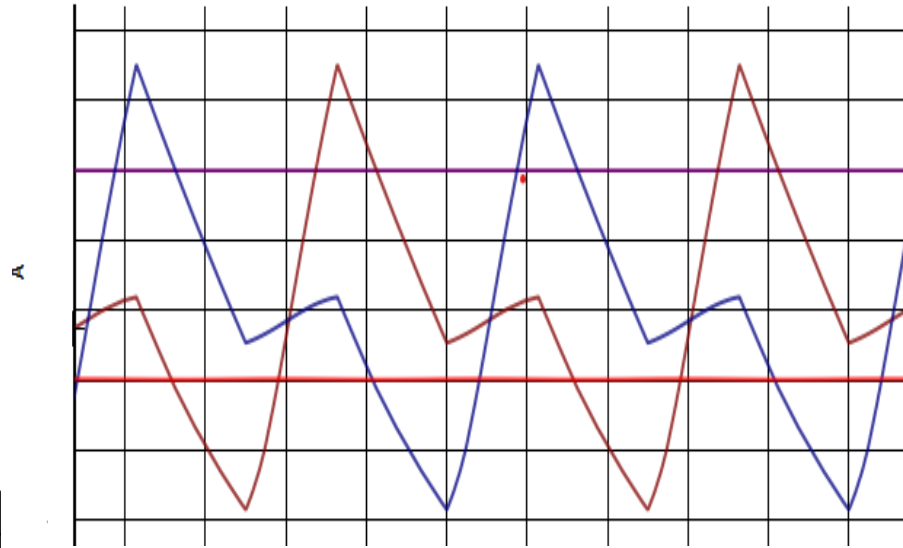
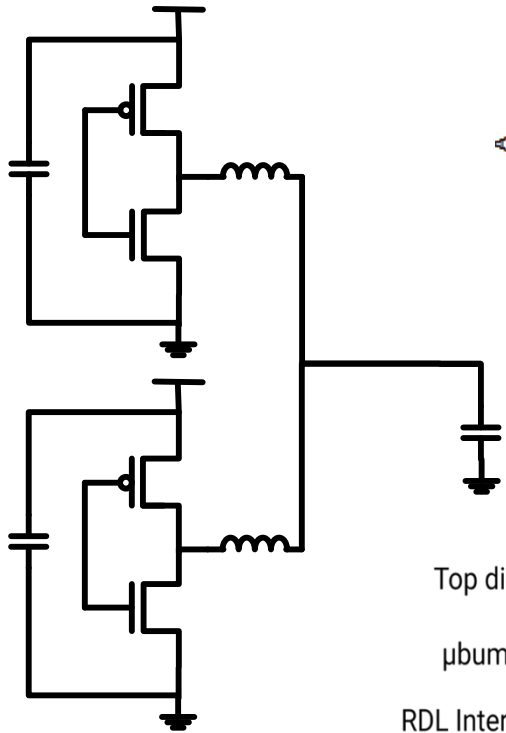
Why, now where



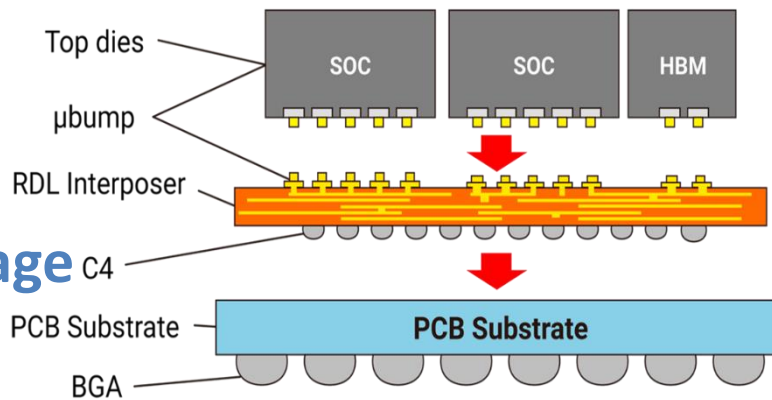
*Calculations are based on hypothetical 2:1 Regulator with 85% Efficiency and 4:1 Regulator at 80% Efficiency system using estimated parasitics and losses from multiple sources

4:1 Switched Inductor

2.8V -> 0.7V



- **Relative Efficiency: Low**
- **Duty ratio drops from 0.5 to 0.25**
- **High Inductor current ripple**
- **Magnetic Stress**



2A~4A/mm²
0.65V

1A~2A/mm²
2.4V ~ 3.6V

In-Package IVR Ingredients

Low Resistance Interconnect

Precision Analog

Power Magnetics

High Density Capacitors

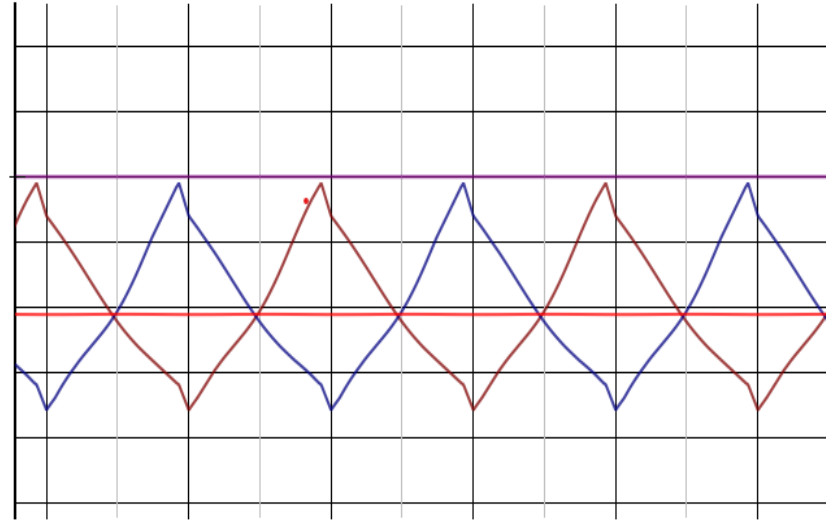
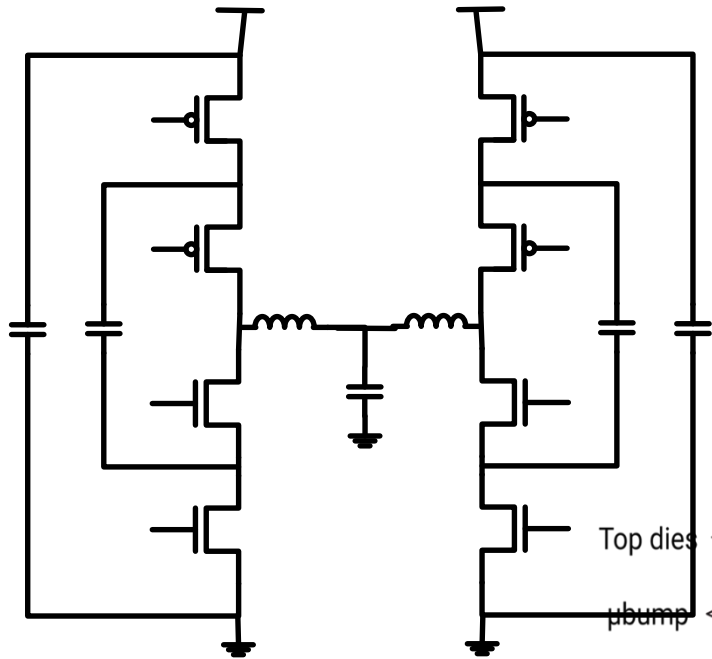
Low Voltage Switch FETs

High Voltage Switch FETs

Requires High Voltage
Transistors

4:1 – 3 Level Buck

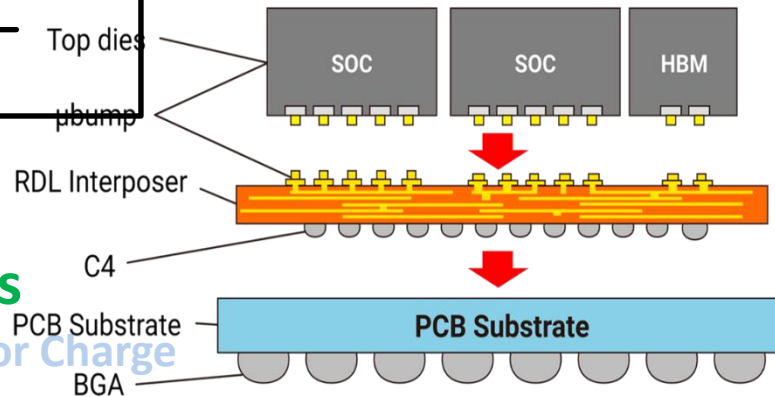
2.8V -> 0.7V



- Efficiency: Good
- Regulator Losses < I^2R Losses

Uses 1.8V Transistors

Circuits to Balance Capacitor Charge



2A~4A/mm²
0.65 V

1A~2A/mm²
2.4 V ~ 3.6V

In-Package IVR Ingredients

Low Resistance Interconnect

Precision Analog

Power Magnetics

High Density Capacitors

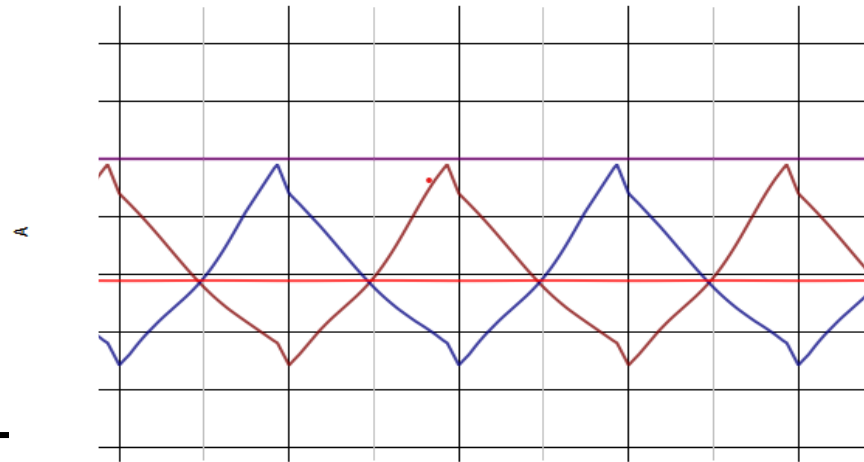
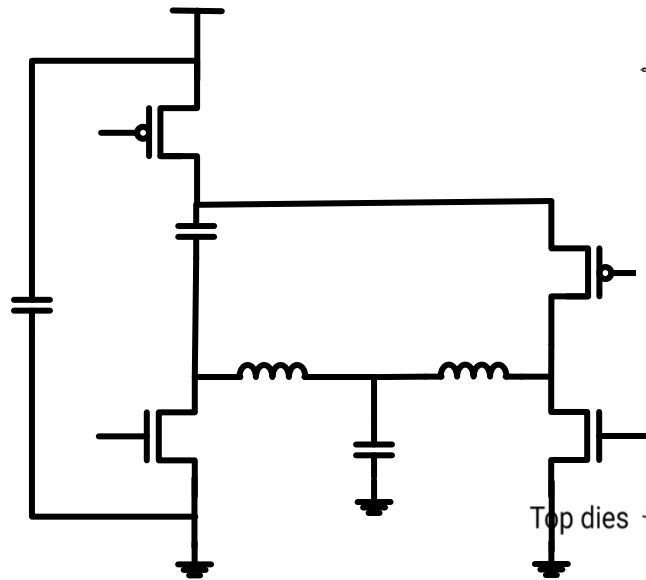
Low Voltage Switch FETs

High Voltage Switch FETs

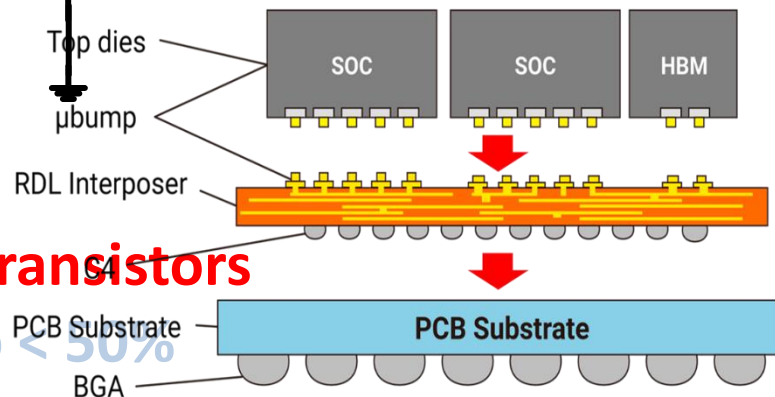
4:1 – Series Capacitor Buck

2.8V -> 0.7V

2-Level 2-Phase Buck



Same Inductor ripple same as 2:1 Buck
4:1 Efficiency: Better than 3-Level



Requires >3.0V Transistors

Conversion Ratio < 50%

2A~4A/mm²
0.65V

1A~2A/mm²
2.4V ~ 3.6V

In-Package IVR Ingredients

Low Resistance Interconnect

Precision Analog

Power Magnetics

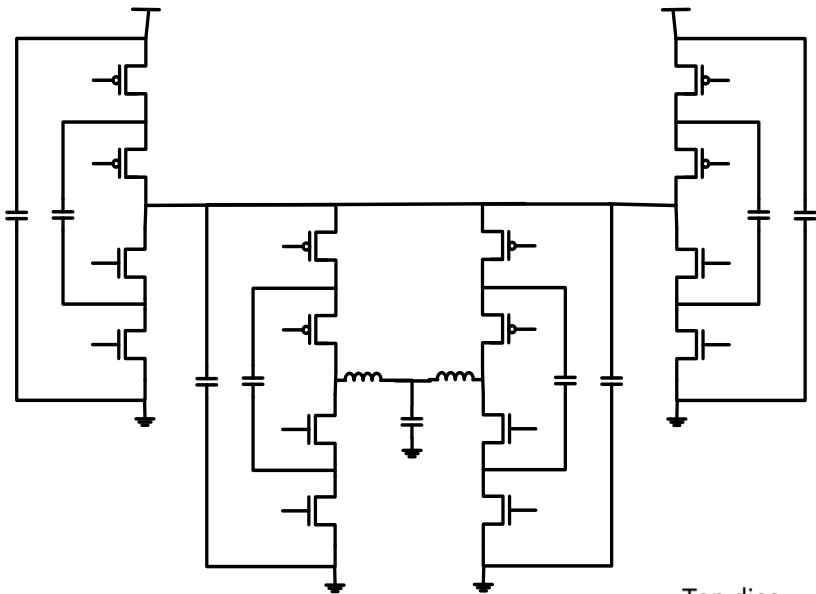
High Density Capacitors

Low Voltage Switch FETs

High Voltage Switch FETs

8:1 – Switch Cap + Switch Inductor

5.6V -> 0.7V

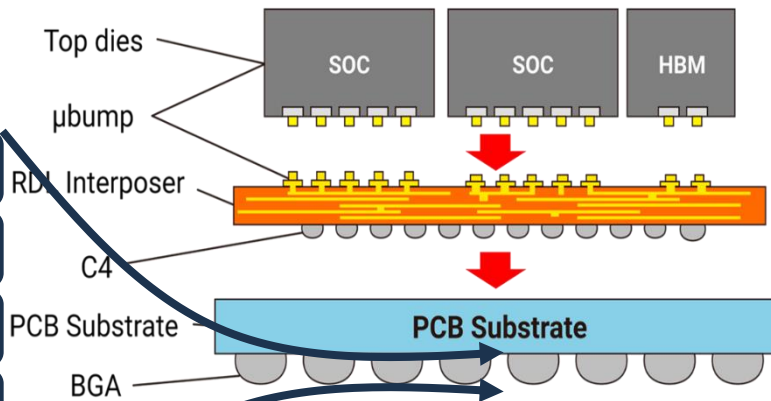


Switch Cap Stage operates Independently
Switch Cap Stage is Un-Regulated 2:1 Charge Pump
Same Inductor ripple as 2:1 Buck
Switch Cap Operates at 1/10 Buck Frequency

Current and Voltage Ripple same as 2:1 Buck
Maintains High Bandwidth Benefits of the Buck

Under-Package IVR Ingredients

- Low Resistance Interconnect
- Precision Analog
- Power Magnetics
- High Density Capacitors
- Low Voltage Switch FETs
- High Voltage Switch FETs



8A~16A/mm²
0.65V

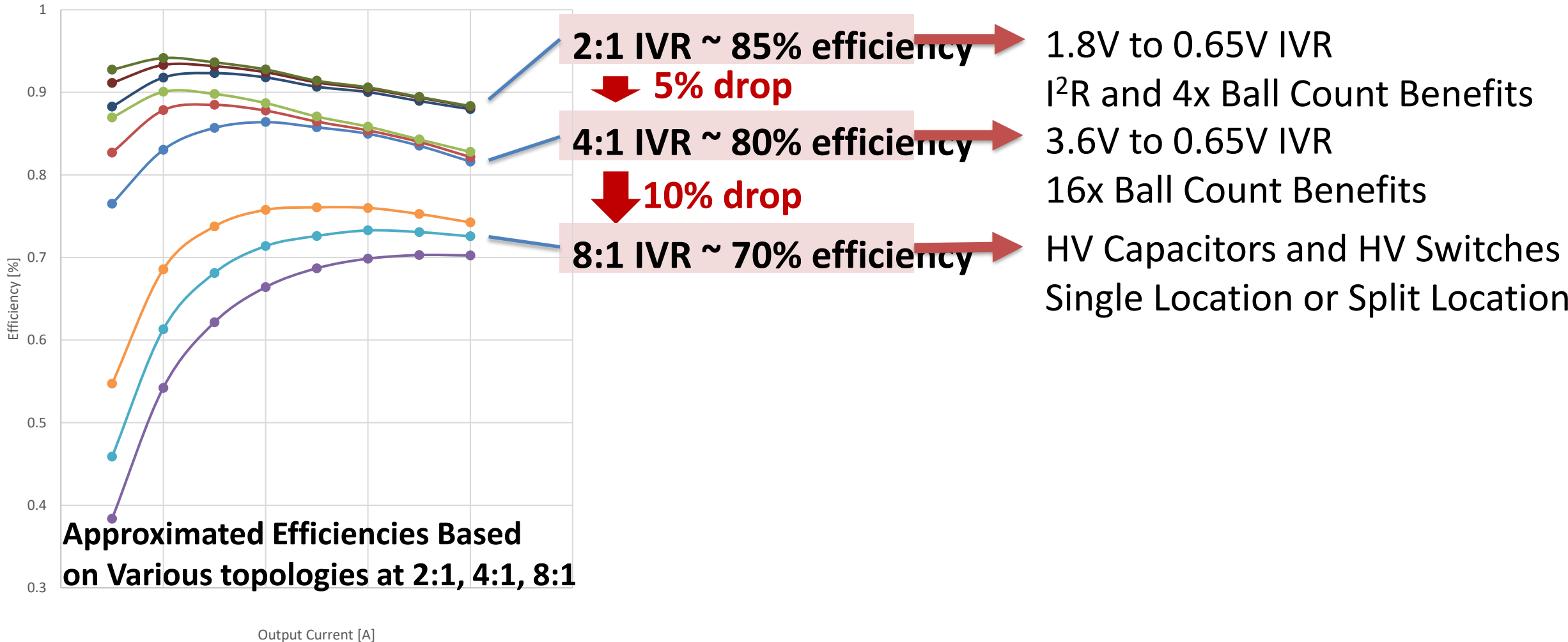
2A~4A/mm²
2.4V ~ 3.6V

1A~2A/mm²
4.8V ~ 7.2V

In-Package IVR Ingredients

- Low Resistance Interconnect
- Precision Analog
- Power Magnetics
- High Density Capacitors
- Low Voltage Switch FETs
- High Voltage Switch FETs

Target Efficiency from 2:1 to 4:1 to 8:1



Approximated Efficiencies Based on Various topologies at 2:1, 4:1, 8:1

Efficiencies are based on estimated switching and conduction losses and are not representative of any particular implementation or solution

Summary

- Vertical power deliver provides a roadmap for scaling power deliver to match the scaling of computing
- In-Package Voltage Regulators benefits reducing the number of solder balls and lowering I^2R losses
- TSMC is providing a roadmap of future technologies to enable IVR implementations that match the industries needs.



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(Optional: Contact Information)